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METHOD AND APPARATUS FOR ETCHING A SEMICONDUCTOR ARTICLE AND METHOD OF PREPARING A SEMICONDUCTOR ARTICLE BY USING THE SAME

ABSTRACT OF THE DISCLOSURE

With a method according to the invention, a semiconductor article such as an SOI substrate having on the surface thereof a single crystal silicon film formed on an insulator is etched by heat treatment in a hydrogen-containing reducing atmosphere in order to remove the surface by a desired height and smooth it. The method is characterized in that the single crystal silicon film is arranged opposite to silicon oxide in a furnace during the etching process.

Figure 1

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